

---

**I<sup>2</sup>C-Compatible, (2-wire) Serial EEPROM**  
**4-Kbit (512 x 8), 8-Kbit (1024 x 8)**

---

**DATASHEET**

---

**Standard Features**

---

- Low-voltage and Standard-voltage Operation
  - $V_{CC} = 1.7V$  to 5.5V
- Internally Organized as 512 x 8 (4K), or 1024 x 8 (8K)
- I<sup>2</sup>C-compatible (2-wire) Serial Interface
- Schmitt Trigger, Filtered Inputs for Noise Suppression
- Bidirectional Data Transfer Protocol
- 1MHz (2.5V, 2.7V, 5V), 400kHz (1.7V) Compatibility
- Write Protect Pin for Hardware Data Protection
- 16-byte Page Write Mode
  - Partial Page Writes Allowed
- Self-timed Write Cycle (5ms Max)
- High-reliability
  - Endurance: 1,000,000 Write Cycles
  - Data Retention: 100 Years
- Green Package Options (Pb/Halide-free/RoHS Compliant)
  - 8-lead PDIP, 8-lead SOIC, 8-lead TSSOP, 8-pad UDFN, 5-lead SOT23, and 8-ball VFBGA
- Die Options: Wafer Form and Tape and Reel

---

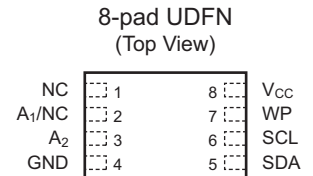
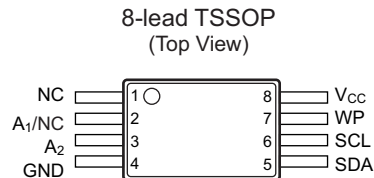
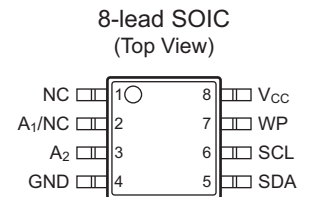
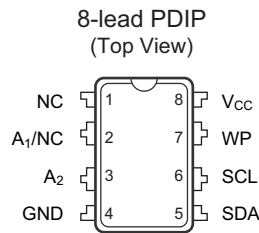
**Description**

---

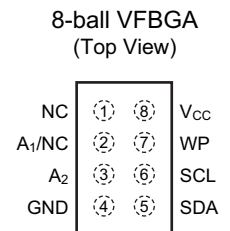
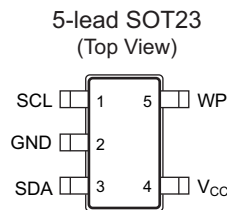
The Atmel® AT24C04C and AT24C08C provides 4,096/8,192 bits of Serial Electrically Erasable and Programmable Read-Only Memory (EEPROM) organized as 512/1024 words of 8 bits each. The device is optimized for use in many industrial and commercial applications where low-power and low-voltage operation are essential. AT24C04C/08C is available in space-saving 8-lead PDIP, 8-lead JEDEC SOIC, 8-lead TSSOP, 8-pad UDFN, 5-lead SOT23, and 8-ball VFBGA packages and is accessed via a 2-wire serial interface.

# 1. Pin Configurations and Pinouts

Pin Name	Function
NC	No Connect
A <sub>1</sub>	Address Input (4K Only)
A <sub>2</sub>	Address Input
SDA	Serial Data
SCL	Serial Clock Input
WP	Write Protect
GND	Ground
V <sub>CC</sub>	Power Supply



- Notes:
- For use of 5-lead SOT23, the software A2 and A1 bits in the device address word must be set to zero to properly communicate.
  - Drawings are note to scale.

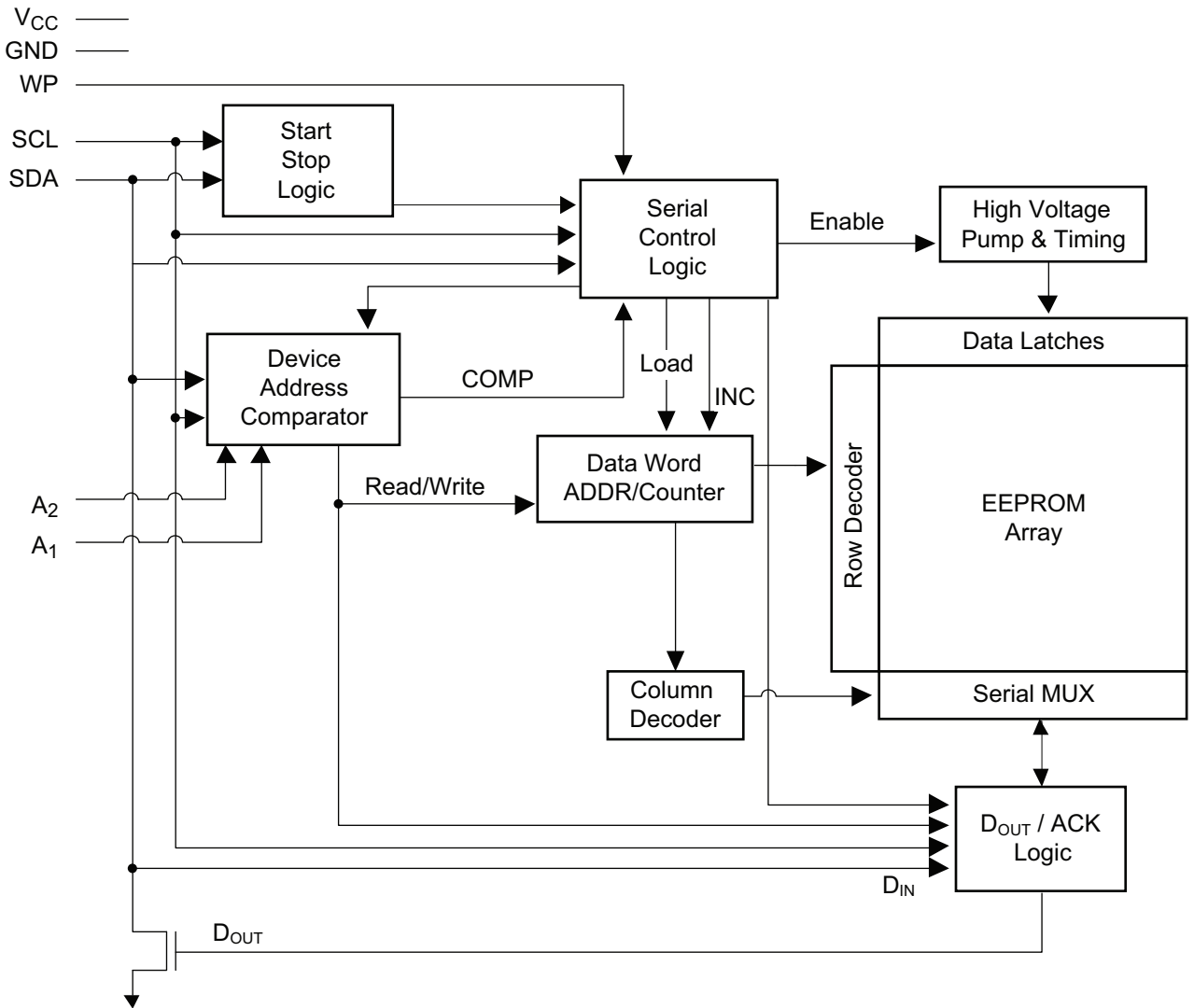


# 2. Absolute Maximum Ratings

Operating Temperature	-55°C to +125°C
Storage Temperature	-65°C to +150°C
Voltage on any pin with respect to ground	-1.0V to +7.0V
Maximum Operating Voltage	6.25V
DC Output Current	.5.0mA

\*Notice: Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### 3. Block Diagram



## 4. Pin Description

**Serial Clock (SCL):** The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.

**Serial Data (SDA):** The SDA pin is bidirectional for serial data transfer. This pin is open-drain driven and may be wire-ORed with any number of other open-drain or open-collector devices.

**Device/Page Addresses (A<sub>2</sub> and A<sub>1</sub>):** The AT24C04C uses the A<sub>2</sub> and A<sub>1</sub> inputs for hard wire addressing allowing a total of four 4K devices to be addressed on a single bus system. Pin 1 is a no connect and can be connected to ground (see [Section 7. “Device Addressing” on page 10](#)). The AT24C08C only uses the A<sub>2</sub> input for hardware addressing and a total of two 8K devices may be addressed on a single bus system. The A<sub>0</sub> and A<sub>1</sub> pins are no connects and can be connected to ground (see [Section 7.](#)).

**Write Protect (WP):** AT24C04C/08C has a Write Protect pin that provides hardware data protection. The Write Protect pin allows normal read/write operations when connected to Ground (GND). When the Write Protect pin is connected to V<sub>CC</sub>, the write protection feature is enabled and operates as shown in [Table 4-1](#).

**Table 4-1. Write Protect**

WP Pin Status	Part of the Array Protected
At V <sub>CC</sub>	Full array
At GND	Normal read/write operations

## 5. Memory Organization

**AT24C04C, 4K Serial EEPROM:** Internally organized with 32 pages of 16 bytes each, the 4K requires a 9-bit data word address for random word addressing.

**AT24C08C, 8K Serial EEPROM:** Internally organized with 64 pages of 16 bytes each, the 8K requires a 10-bit data word address for random word addressing.

**Table 5-1. Pin Capacitance<sup>(1)</sup>**

Applicable over recommended operating range from  $T_A = 25^\circ\text{C}$ ,  $f = 1.0\text{MHz}$ ,  $V_{CC} = +1.7\text{V}$  to  $+5.5\text{V}$ .

Symbol	Test Condition	Max	Units	Conditions
$C_{I/O}$	Input/Output capacitance (SDA)	8	pF	$V_{I/O} = 0\text{V}$
$C_{IN}$	Input capacitance ( $A_0, A_1, A_2, \text{SCL}$ )	6	pF	$V_{IN} = 0\text{V}$

Note: 1. This parameter is characterized and is not 100% tested.

**Table 5-2. DC Characteristics**

Applicable over recommended operating range from:  $T_{AI} = -40^\circ\text{C}$  to  $+85^\circ\text{C}$ ,  $V_{CC} = +1.7\text{V}$  to  $+5.5\text{V}$  (unless otherwise noted).

Symbol	Parameter	Test Condition	Min	Typ	Max	Units
$V_{CC1}$	Supply Voltage		1.7		5.5	V
$V_{CC2}$	Supply Voltage		4.5		5.5	V
$I_{CC}$	Supply Current $V_{CC} = 5.0\text{V}$	Read at 100kHz		0.4	1.0	mA
$I_{CC}$	Supply Current $V_{CC} = 5.0\text{V}$	Write at 100kHz		2.0	3.0	mA
$I_{SB1}$	Standby Current $V_{CC} = 1.7\text{V}$	$V_{IN} = V_{CC}$ or $V_{SS}$			1.0	$\mu\text{A}$
$I_{SB2}$	Standby Current $V_{CC} = 5.5\text{V}$	$V_{IN} = V_{CC}$ or $V_{SS}$			6.0	$\mu\text{A}$
$I_{LI}$	Input Leakage Current	$V_{IN} = V_{CC}$ or $V_{SS}$		0.10	3.0	$\mu\text{A}$
$I_{LO}$	Output Leakage Current	$V_{OUT} = V_{CC}$ or $V_{SS}$		0.05	3.0	$\mu\text{A}$
$V_{IL}$	Input Low Level <sup>(1)</sup>		-0.6		$V_{CC} \times 0.3$	V
$V_{IH}$	Input High Level <sup>(1)</sup>		$V_{CC} \times 0.7$		$V_{CC} + 0.5$	V
$V_{OL2}$	Output Low Level $V_{CC} = 3.0\text{V}$	$I_{OL} = 2.1\text{mA}$			0.4	V
$V_{OL1}$	Output Low Level $V_{CC} = 1.7\text{V}$	$I_{OL} = 0.15\text{mA}$			0.2	V

Note: 1.  $V_{IL}$  min and  $V_{IH}$  max are reference only and are not tested.

**Table 5-3. AC Characteristics**

Applicable over recommended operating range from  $T_{AI} = -40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$ ,  $V_{CC} = +1.7\text{V}$  to  $+5.5\text{V}$ ,  $CL = 1\text{TTL Gate and } 100\text{pF}$  (unless otherwise noted).

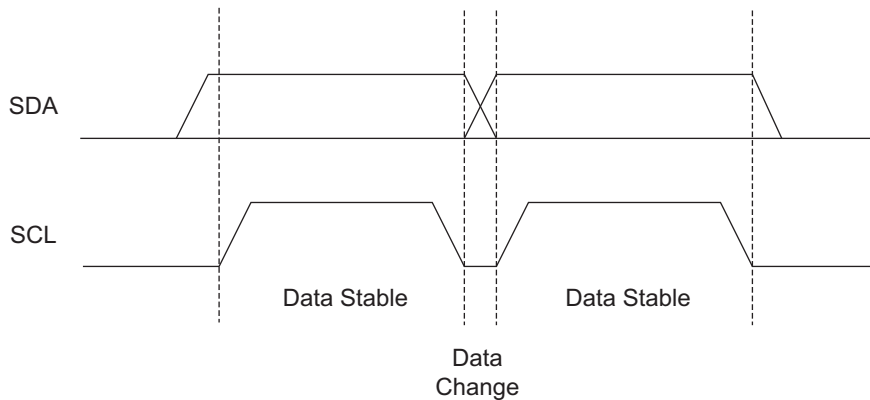
Symbol	Parameter	1.7V		2.5V, 2.7V, 5.0V		Units
		Min	Max	Min	Max	
$f_{SCL}$	Clock Frequency, SCL		400		1000	kHz
$t_{LOW}$	Clock Pulse Width Low	1.2		0.4		$\mu\text{s}$
$t_{HIGH}$	Clock Pulse Width High	0.6		0.4		$\mu\text{s}$
$t_I$	Noise Suppression Time		100		50	ns
$t_{AA}$	Clock Low to Data Out Valid	0.1	0.9	0.05	0.55	$\mu\text{s}$
$t_{BUF}$	Time the bus must be free before a new transmission can start.	1.2		0.5		$\mu\text{s}$
$t_{HD.STA}$	Start Hold Time	0.6		0.25		$\mu\text{s}$
$t_{SU.STA}$	Start Setup Time	0.6		0.25		$\mu\text{s}$
$t_{HD.DAT}$	Data In Hold Time	0		0		$\mu\text{s}$
$t_{SU.DAT}$	Data In Setup Time	100		100		ns
$t_R$	Inputs Rise Time <sup>(1)</sup>		0.3		0.3	$\mu\text{s}$
$t_F$	Inputs Fall Time <sup>(1)</sup>		300		100	ns
$t_{SU.STO}$	Stop Setup Time	0.6		.25		$\mu\text{s}$
$t_{DH}$	Data Out Hold Time	50		50		ns
$t_{WR}$	Write Cycle Time		5		5	ms
Endurance <sup>(1)</sup>	3.3V, $+25^{\circ}\text{C}$ , Page Mode	1,000,000				Write Cycles

Note: 1. This parameter is ensured by characterization only.

## 6. Device Operation

**Clock and Data Transitions:** The SDA pin is normally pulled high with an external device. Data on the SDA pin may change only during SCL low time periods. Data changes during SCL high periods will indicate a Start or Stop condition as defined below.

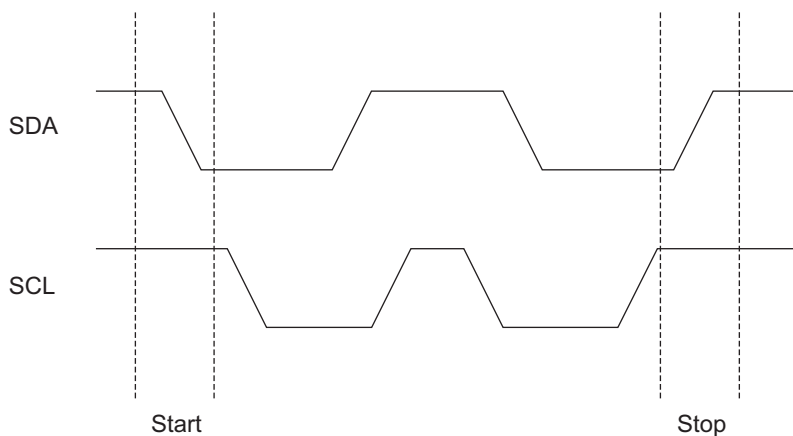
**Figure 6-1. Data Validity**



**Start Condition:** A high-to-low transition of SDA with SCL high is a Start condition which must precede any other command.

**Stop Condition:** A low-to-high transition of SDA with SCL high is a Stop condition. After a read sequence, the Stop command will place the EEPROM in a standby power mode.

**Figure 6-2. Start and Stop Definition**

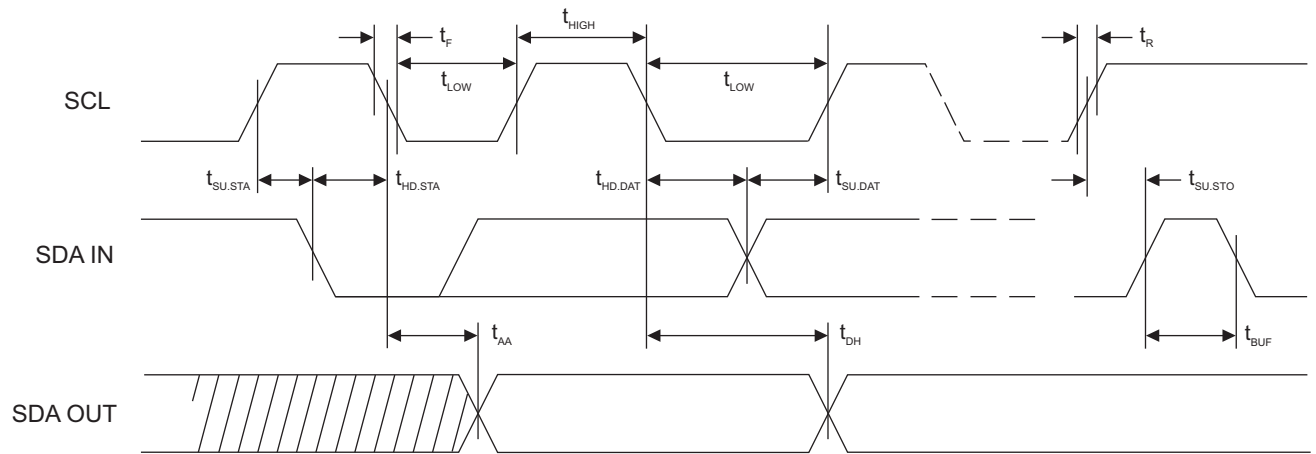






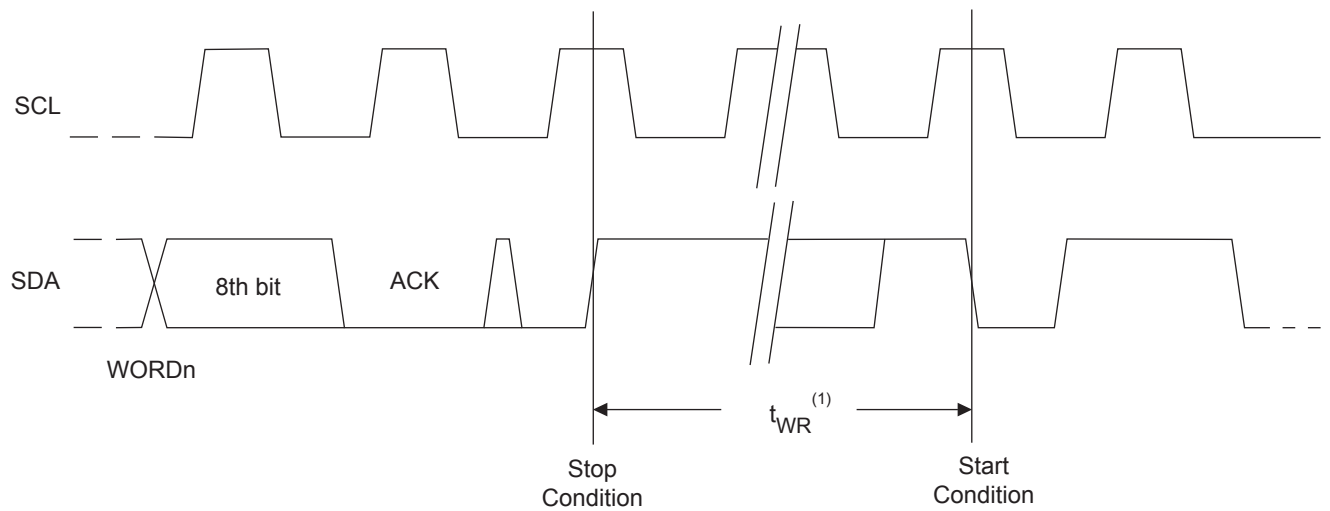
**Figure 6-5. Bus Timing**

SCL: Serial Clock, SDA: Serial Data I/O



**Figure 6-6. Write Cycle Timing**

SCL: Serial Clock, SDA: Serial Data I/O



Notes: 1. The write cycle time  $t_{WR}$  is the time from a valid Stop condition of a write sequence to the end of the internal clear/write cycle.

## 7. Device Addressing

**Standard EEPROM Access:** The 4K and 8K EEPROM device requires an 8-bit device address word following a start condition to enable the chip for a read or write operation. The device address word consists of a mandatory “1010” (0xA) sequence for the first four Most Significant Bits (MSB) as shown in [Figure 7-1](#). This is common to all the EEPROM devices.

The 4K EEPROM only uses the A2 and A1 device address bits with the third bit being a memory page address bit. The two device address bits must compare to their corresponding hard-wired input pins. The A<sub>0</sub> pin is no connect.

The 8K EEPROM only uses the A2 device address bit with the next two bits being for memory page addressing. The A2 address bit must compare to its corresponding hard-wired input pin. The A<sub>1</sub> and A<sub>0</sub> pins are no connect.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

Upon a compare of the device address, the EEPROM will output a zero. If a compare is not made, the chip will return to a standby state.

For the SOT23 package offering, the 4K EEPROM software A2 and A1 bits in the device address word must be set to zero to properly communicate. The 8K EEPROM software A2 bit in the device address word must be set to zero to properly communicate.

**Figure 7-1. Device Address**

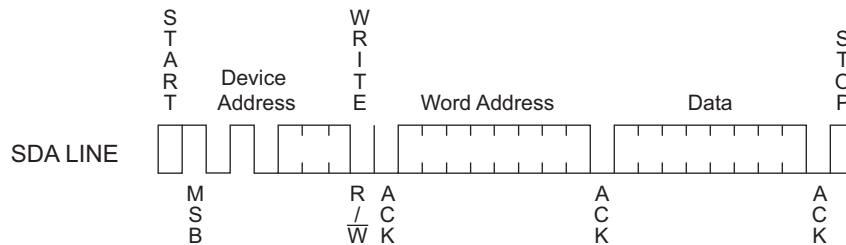
Density	Access Area	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
4K	EEPROM	1	0	1	0	A <sub>2</sub>	A <sub>1</sub>	P0	R/W
8K	EEPROM	1	0	1	0	A <sub>2</sub>	P1	P0	R/W

MSB LSB

## 8. Write Operations

**Byte Write:** A write operation requires an 8-bit data word address following the device address word and acknowledgment. Upon receipt of this address, the EEPROM will again respond with a zero and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a zero and the addressing device, such as a microcontroller, must terminate the write sequence with a Stop condition. At this time the EEPROM enters an internally timed write cycle,  $t_{WR}$ , to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the write is complete.

**Figure 8-1. Byte Write**

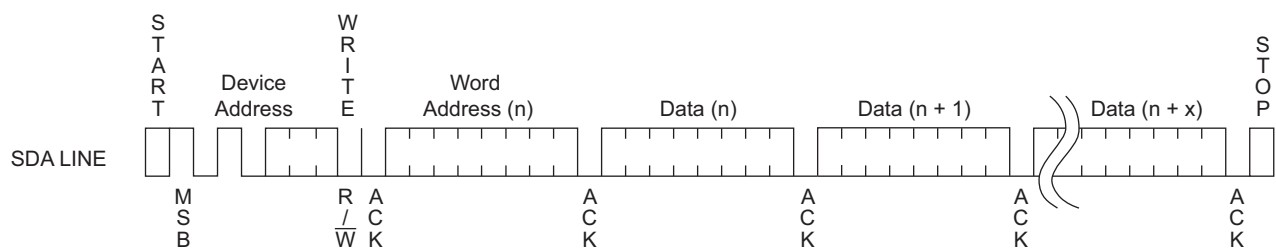


**Page Write:** The 4K and 8K EEPROM devices are capable of a 16-byte Page Write.

A Page Write is initiated in the same way as a Byte Write, but the microcontroller does not send a Stop condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to fifteen more data words. The EEPROM will respond with a zero after each data word received. The microcontroller must terminate the Page Write sequence with a Stop condition.

The data word address lower four bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than 16 data words are transmitted to the EEPROM, the data word address will “roll over” and previous data will be overwritten.

**Figure 8-2. Page Write**



**Acknowledge Polling:** Once the internally timed write cycle has started and the EEPROM inputs are disabled, Acknowledge Polling can be initiated. This involves sending a Start condition followed by the device address word. The Read/Write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a zero allowing the read or write sequence to continue.

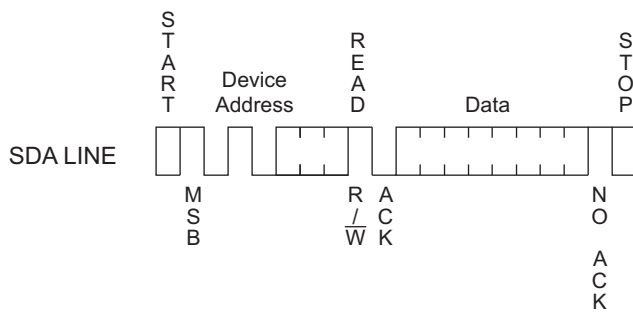
## 9. Read Operations

Read operations are initiated in the same way as write operations with the exception that the read/write select bit in the device address word is set to one. There are three read operations: Current Address Read, Random Address Read, and Sequential Read.

**Current Address Read:** The internal data word address counter maintains the last address accessed during the last read or write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address roll-over during read is from the last byte of the last memory page to the first byte of the first page. The address roll-over during write is from the last byte of the current page to the first byte of the same page.

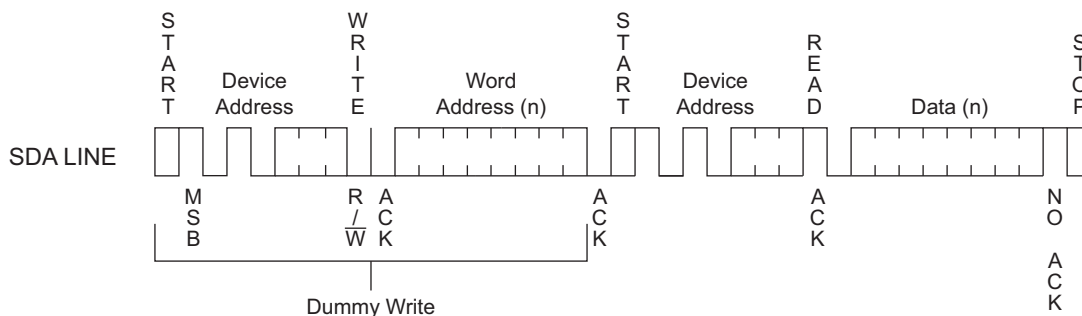
Once the device address with the read/write select bit set to one is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input zero but does generate a following stop condition.

**Figure 9-1. Current Address Read**



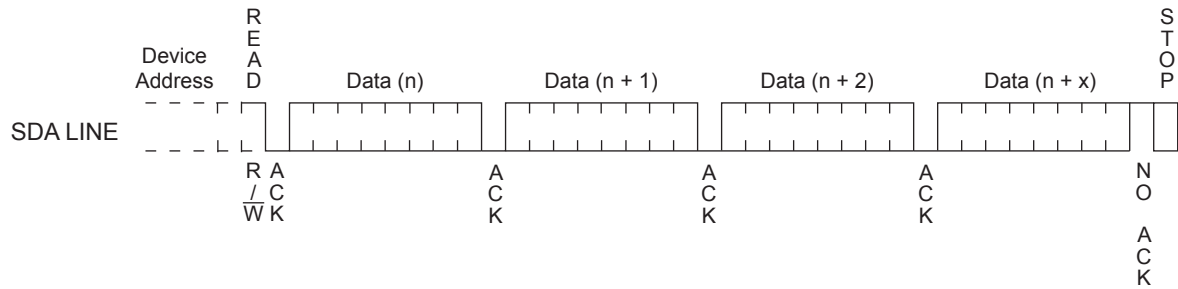
**Random Read:** A random read requires a “dummy” byte write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another start condition. The microcontroller now initiates a Current Address Read by sending a device address with the read/write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a zero but does generate a following stop condition.

**Figure 9-2. Random Read**

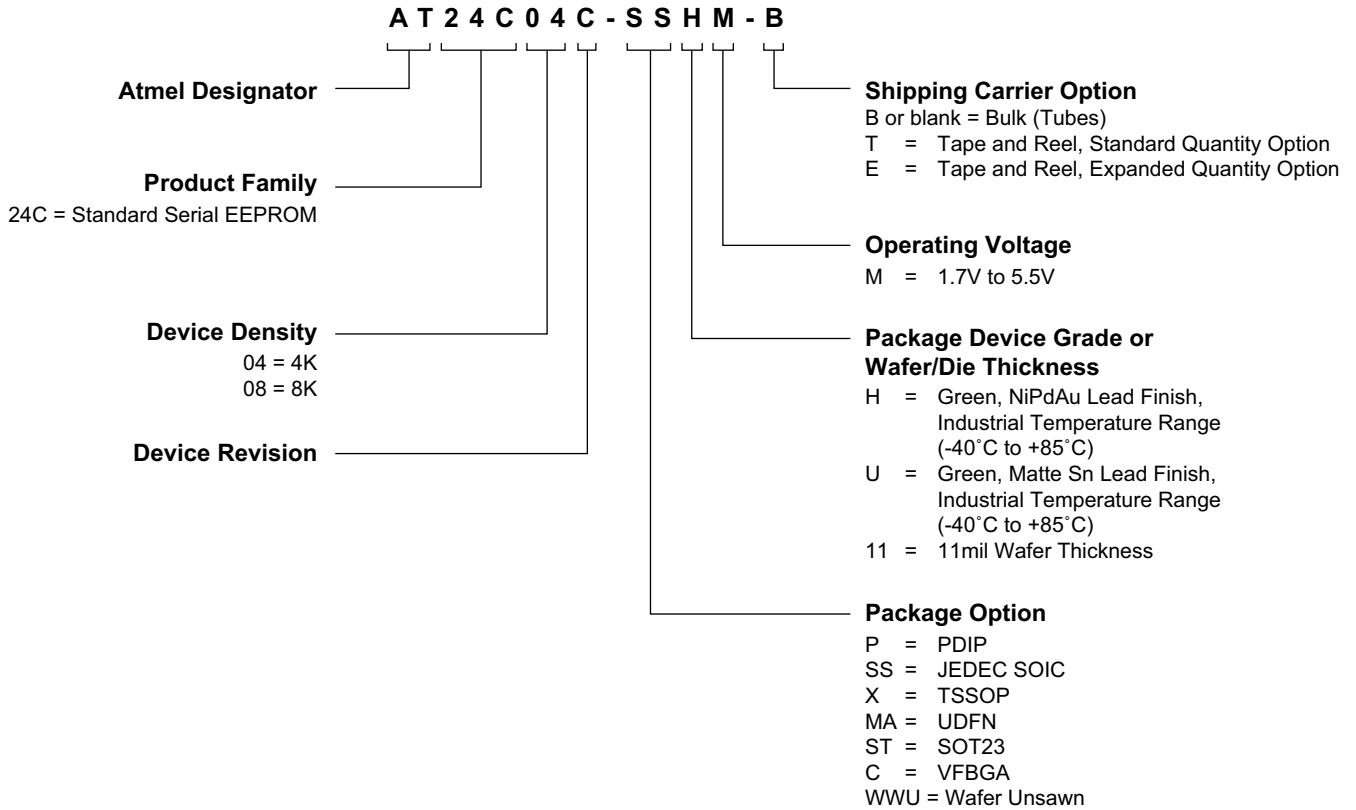


**Sequential Read:** Sequential Reads are initiated by either a Current Address Read or a Random Address Read. After the microcontroller receives a data word, it responds with an Acknowledge. As long as the EEPROM receives an Acknowledge, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will roll-over and the Sequential Read will continue. The Sequential Read operation is terminated when the microcontroller does not respond with a zero but does generate a following Stop condition.

**Figure 9-3. Sequential Read**



## 10. Ordering Code Detail



# 11. Product Markings

## AT24C04C and AT24C08C: Package Marking Information

<p>8-lead PDIP</p>	<p>8-lead SOIC</p>	<p>8-lead TSSOP</p>
<p>8-lead UDFN</p> <p>2.0 x 3.0 mm Body</p>	<p>5-lead SOT-23</p>	<p>8-ball VFBGA</p> <p>1.5 x 2.0 mm Body</p>

Note 1: ● designates pin 1

Note 2: Package drawings are not to scale

<b>Catalog Number Truncation</b>			
AT24C04C		Truncation Code ###: 04C	
AT24C08C		Truncation Code ###: 08C	
<b>Date Codes</b>			<b>Voltages</b>
Y = Year	M = Month	WW = Work Week of Assembly	M: 1.7V min
2: 2012    6: 2016	A: January	02: Week 2	
3: 2013    7: 2017	B: February	04: Week 4	
4: 2014    8: 2018	...	...	
5: 2015    9: 2019	L: December	52: Week 52	
<b>Country of Assembly</b>		<b>Lot Number</b>	<b>Grade/Lead Finish Material</b>
@ = Country of Assembly		AAA...A = Atmel Wafer Lot Number	U: Industrial/Matte Tin H: Industrial/NiPdAu
<b>Trace Code</b>			<b>Atmel Truncation</b>
XX = Trace Code (Atmel Lot Numbers Correspond to Code) Example: AA, AB.... YZ, ZZ			AT: Atmel ATM: Atmel ATML: Atmel

5/01/12

<p>Package Mark Contact: DL-CSO-Assy_eng@atmel.com</p>	TITLE	DRAWING NO.	REV.
	24C04-08CSM, AT24C04C and AT24C08C Package Marking Information	24C04-08CSM	B

## 12. Ordering Information

Atmel Ordering Code	Lead Finish	Package	Delivery Information		Operation Range
			Form	Quantity	
AT24C04C-SSHM-B	NiPdAu (Lead-free/Halogen-free)	8S1	Bulk (Tubes)	100 per Tube	Industrial Temperature (-40°C to 85°C)
AT24C04C-SSHM-T			Tape and Reel	4,000 per Reel	
AT24C04C-XHM-B		8X	Bulk (Tubes)	100 per Tube	
AT24C04C-XHM-T			Tape and Reel	5,000 per Reel	
AT24C04C-MAHM-T		8MA2	Tape and Reel	5,000 per Reel	
AT24C04C-MAHM-E			Tape and Reel	15,000 per Reel	
AT24C04C-PUM	Matte Tin (Lead-free/Halogen-free)	8P3	Bulk (Tubes)	50 per Tube	
AT24C04C-STUM-T		5TS1	Tape and Reel	5,000 per Reel	
AT24C04C-CUM-T	SnAgCu Ball (Lead-free/Halogen-free)	8U3-1	Tape and Reel	5,000 per Reel	
AT24C04C-WWU11M <sup>(1)</sup>	N/A	Wafer Sale	Note 1		
<b>AT24C08C Series</b>					
AT24C08C-SSHM-B	NiPdAu (Lead-free/Halogen-free)	8S1	Bulk (Tubes)	100 per Tube	Industrial Temperature (-40°C to 85°C)
AT24C08C-SSHM-T			Tape and Reel	4,000 per Reel	
AT24C08C-XHM-B		8X	Bulk (Tubes)	100 per Tube	
AT24C08C-XHM-T			Tape and Reel	5,000 per Reel	
AT24C08C-MAHM-T		8MA2	Tape and Reel	5,000 per Reel	
AT24C08C-MAHM-E			Tape and Reel	15,000 per Reel	
AT24C08C-PUM	Matte Tin (Lead-free/Halogen-free)	8P3	Bulk (Tubes)	50 per Tube	
AT24C08C-STUM-T		5TS1	Tape and Reel	5,000 per Reel	
AT24C08C-CUM-T	SnAgCu Ball (Lead-free/Halogen-free)	8U3-1	Tape and Reel	5,000 per Reel	
AT24C08C-WWU11M <sup>(1)</sup>	N/A	Wafer Sale	Note 1		

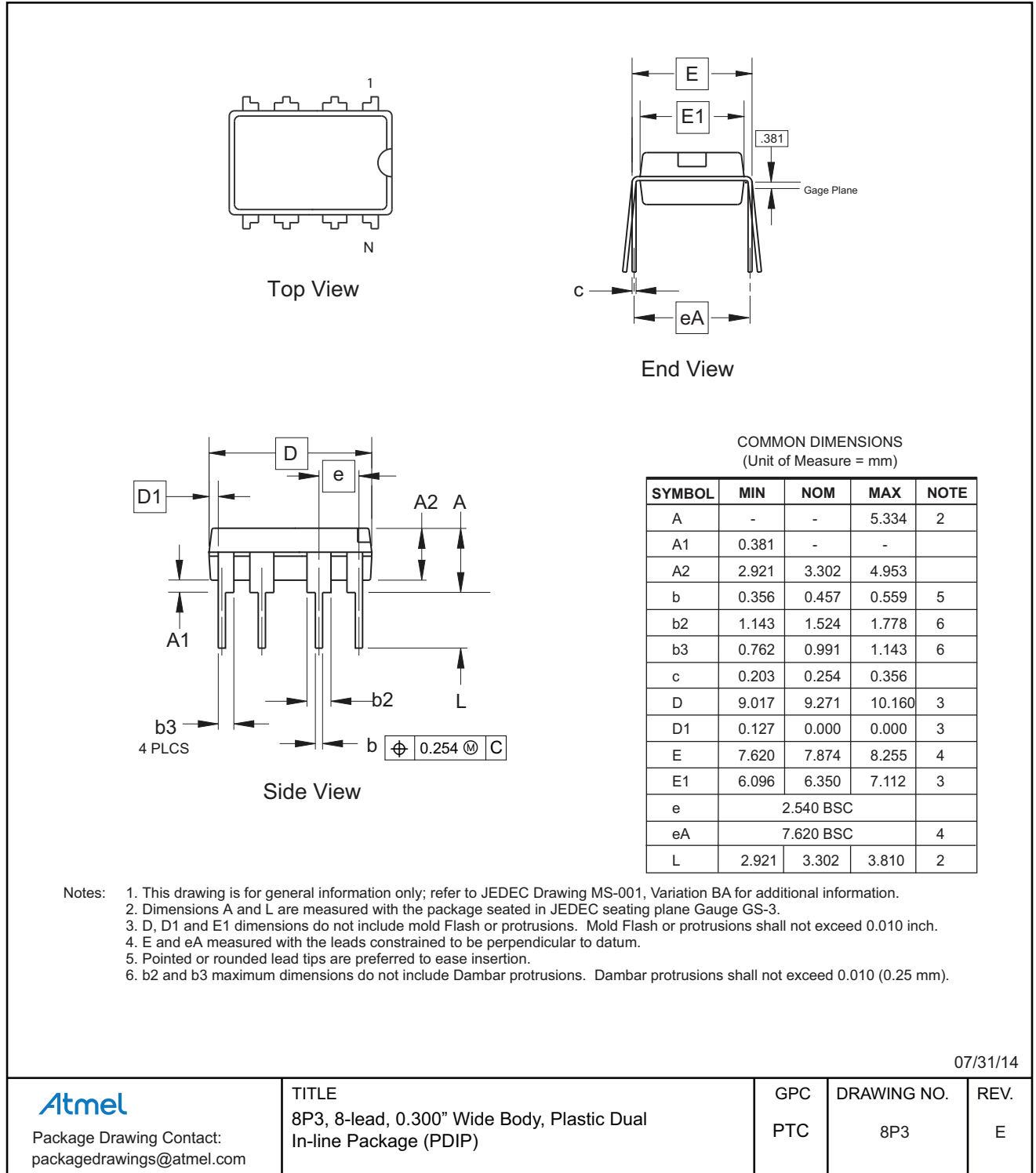
Note: 1. For Wafer sales, please contact Atmel Sales.

Package Type	
<b>8P3</b>	8-lead, 0.300" wide, Plastic Dual Inline Package (PDIP)
<b>8S1</b>	8-lead, 0.150" wide, Plastic Gull Wing Small Outline (JEDEC SOIC)
<b>8X</b>	8-lead, 4.4mm body, Plastic Thin Shrink Small Outline Package (TSSOP)
<b>8MA2</b>	8-pad, 2.00mm x 3.00mm body, 0.50mm pitch, Plastic Ultra Thin Dual Flat No Lead (UDFN)
<b>5TS1</b>	5-lead, 2.90mm x 1.60mm body, Plastic Thin Shrink Small Outline (SOT23)
<b>8U3-1</b>	8-ball, 1.50mm x 2.00mm body, 0.50mm pitch, Die Ball Grid Array (VFPGA)

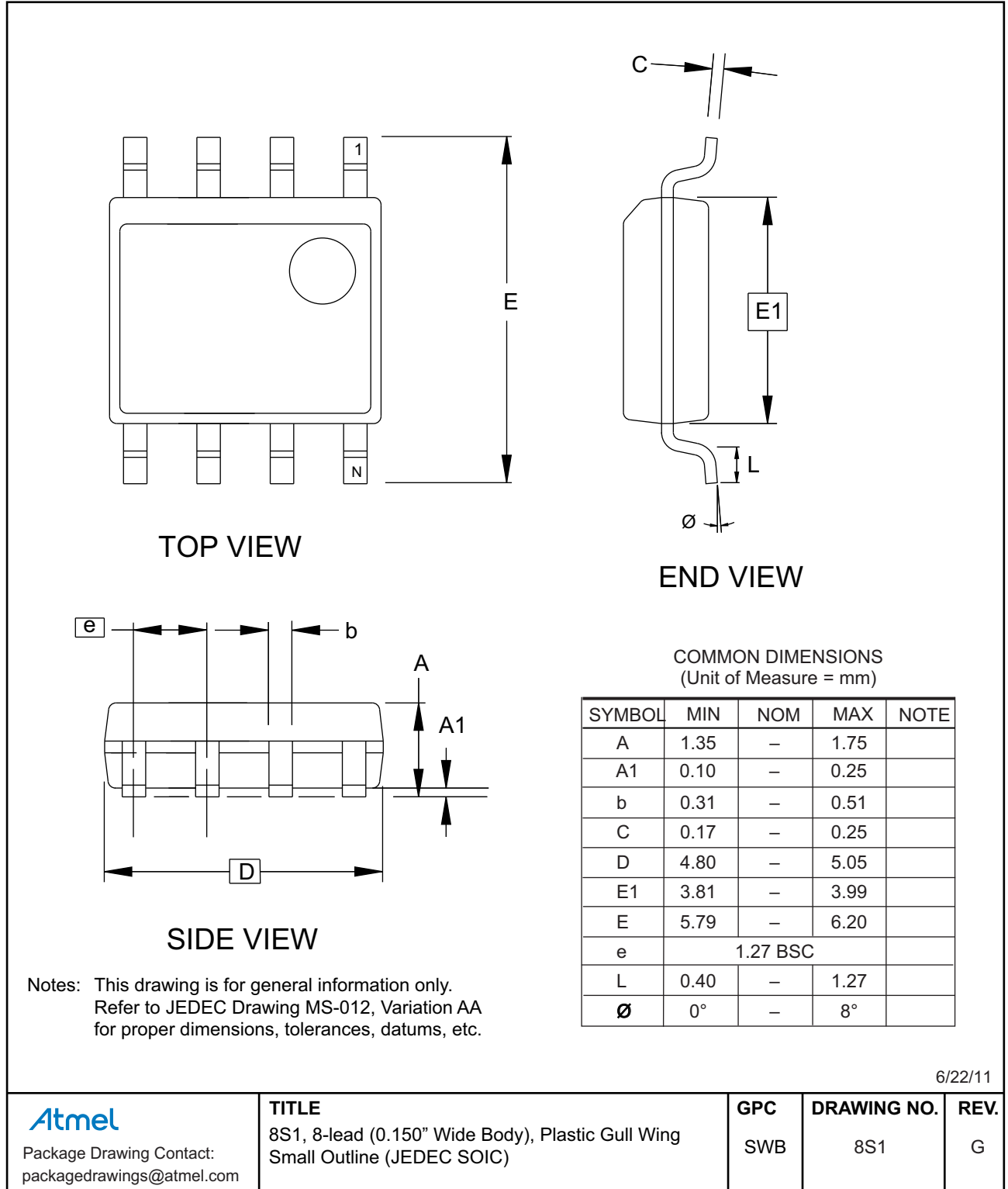


## 13. Packaging Information

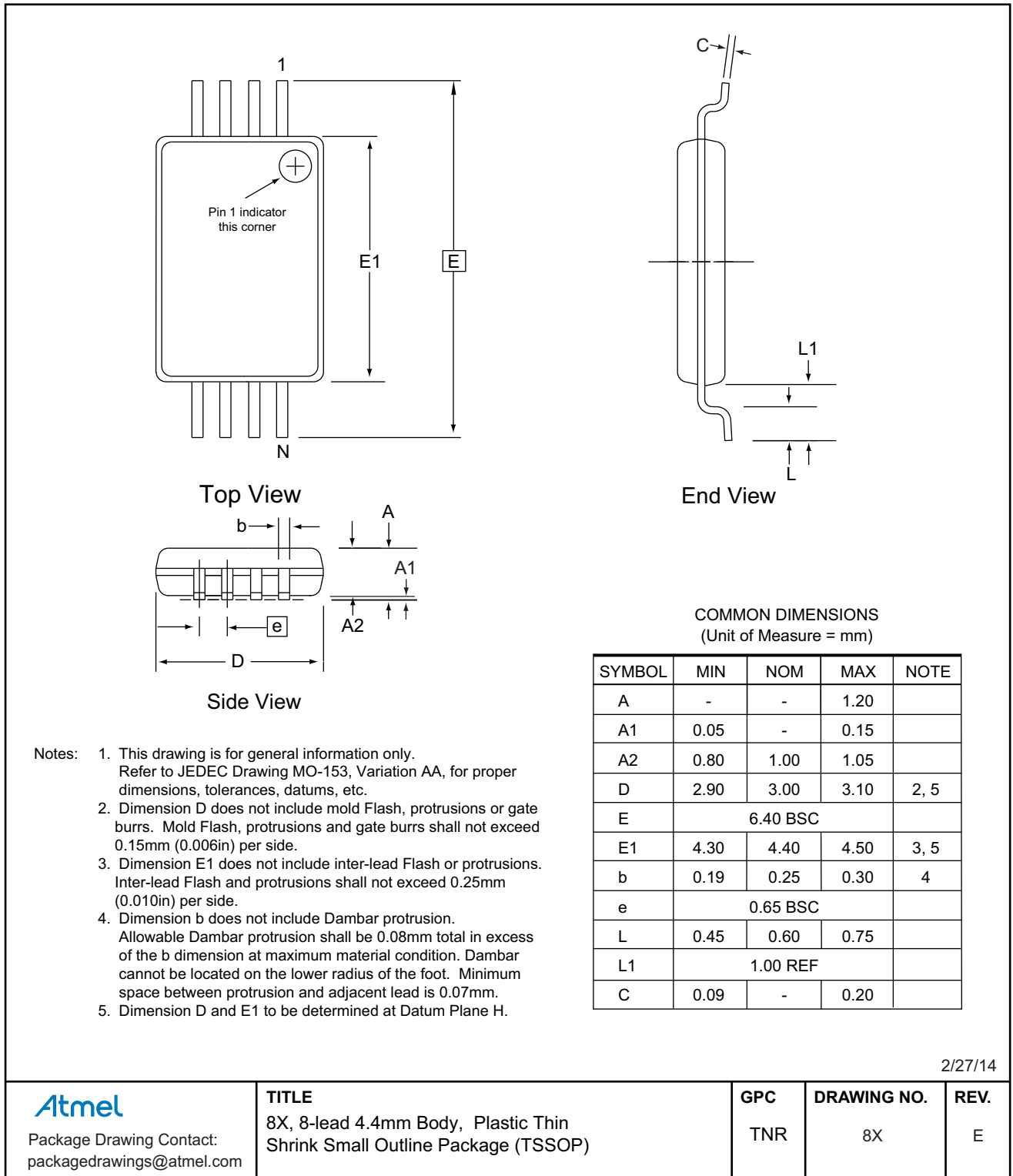
### 13.1 8P3 — 8-lead PDIP



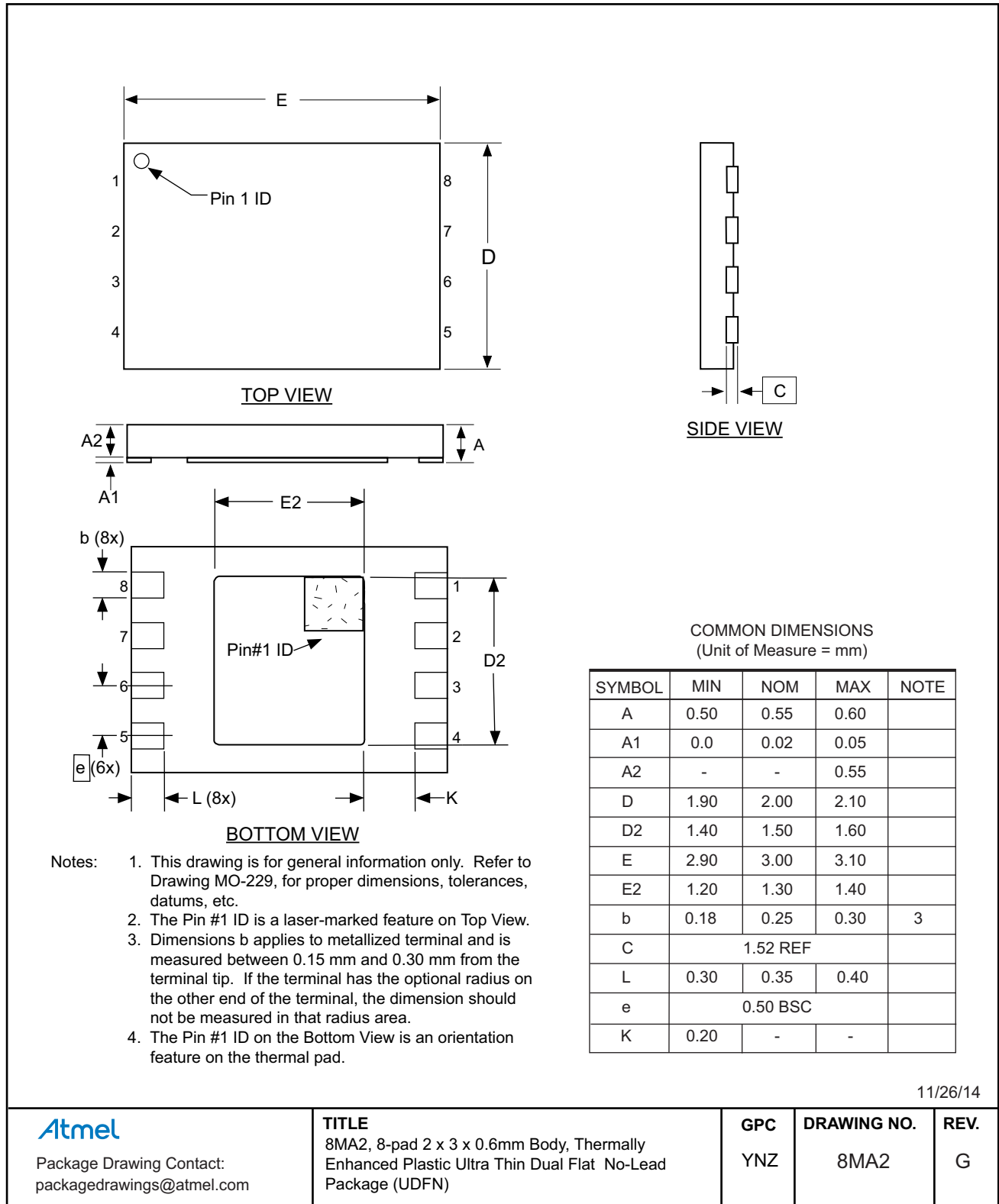
## 13.2 8S1 — 8-lead JEDEC SOIC



### 13.3 8X — 8-lead TSSOP



### 13.4 8MA2 — 8-pad UDFN



11/26/14

**Atmel**

Package Drawing Contact:  
packagedrawings@atmel.com

**TITLE**

8MA2, 8-pad 2 x 3 x 0.6mm Body, Thermally Enhanced Plastic Ultra Thin Dual Flat No-Lead Package (UDFN)

**GPC**

YNZ

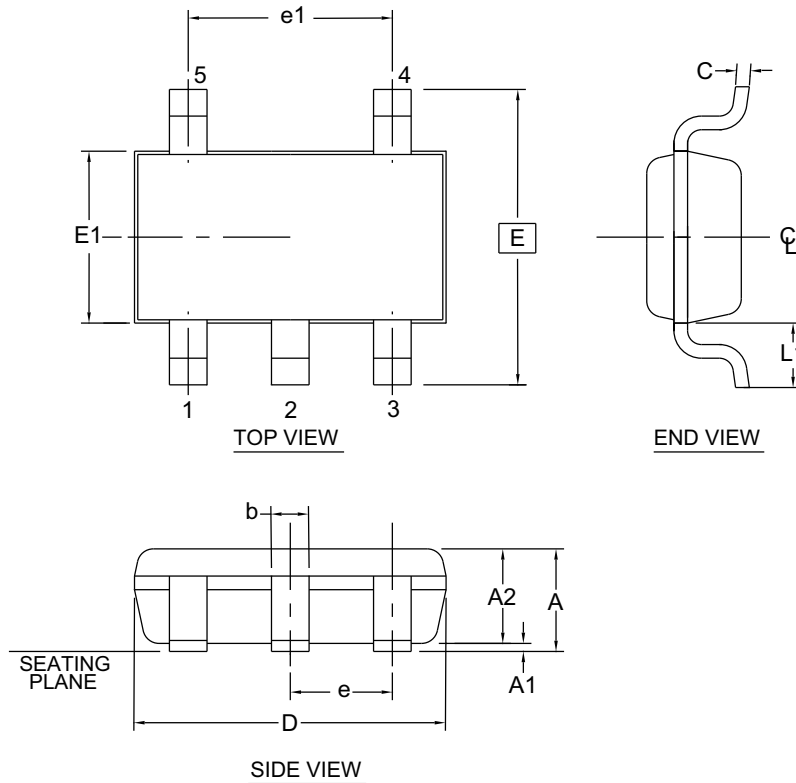
**DRAWING NO.**

8MA2

**REV.**

G

### 13.5 5TS1 — 5-lead SOT23



1. Dimension D does not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15 mm per end. Dimension E1 does not include interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.15 mm per side.
2. The package top may be smaller than the package bottom. Dimensions D and E1 are determined at the outermost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.
3. These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.
4. Dimension "b" does not include dambar protrusion. Allowable dambar protrusion shall be 0.08 mm total in excess of the "b" dimension at maximum material condition. The dambar cannot be located on the lower radius of the foot. Minimum space between protrusion and an adjacent lead shall not be less than 0.07 mm.

This drawing is for general information only. Refer to JEDEC Drawing MO-193, Variation AB for additional information.

COMMON DIMENSIONS  
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	-	-	1.00	
A1	0.00	-	0.10	
A2	0.70	0.90	1.00	
c	0.08	-	0.20	3
D	2.90 BSC			1,2
E	2.80 BSC			1,2
E1	1.60 BSC			1,2
L1	0.60 REF			
e	0.95 BSC			
e1	1.90 BSC			
b	0.30	-	0.50	3,4

5/31/12

**Atmel**

Package Drawing Contact:  
packagedrawings@atmel.com

TITLE

5TS1, 5-lead 1.60mm Body, Plastic Thin Shrink Small Outline Package (Shrink SOT)

GPC

TSZ

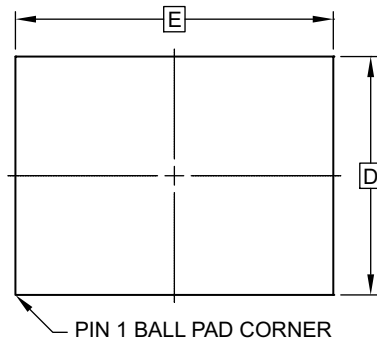
DRAWING NO.

5TS1

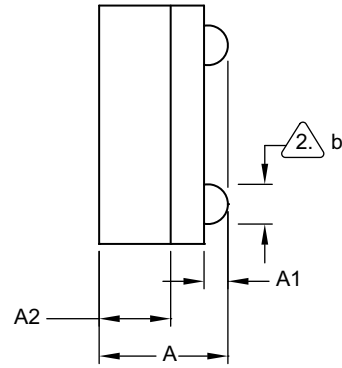
REV.

D

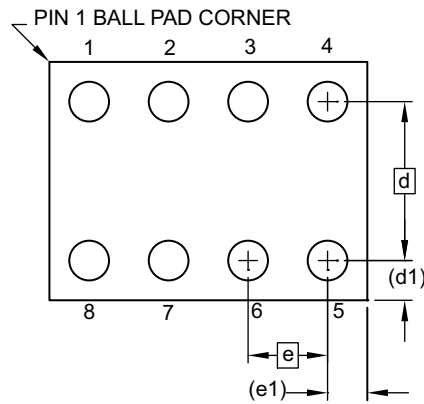
### 13.6 8U3-1 — 8-ball VFBGA



TOP VIEW



SIDE VIEW



BOTTOM VIEW  
8 SOLDER BALLS


**Notes:**

1. This drawing is for general information only.
2. Dimension 'b' is measured at maximum solder ball diameter.
3. Solder ball composition shall be 95.5Sn-4.0Ag-.5Cu.

COMMON DIMENSIONS  
(Unit of Measure - mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	0.73	0.79	0.85	
A1	0.09	0.14	0.19	
A2	0.40	0.45	0.50	
b	0.20	0.25	0.30	2
D	1.50 BSC			
E	2.0 BSC			
e	0.50 BSC			
e1	0.25 REF			
d	1.00 BSC			
d1	0.25 REF			

6/11/13

 Package Drawing Contact: packagedrawings@atmel.com	TITLE 8U3-1, 8-ball, 1.50mm x 2.00mm body, 0.50mm pitch, Very Thin, Fine-Pitch Ball Grid Array Package (VFBGA)	GPC	DRAWING NO.	REV.
		GXU	8U3-1	F

## 14. Revision History

Doc. Rev.	Date	Comments
8787E	01/2015	Add the UDFN expanded quantity options and update the ordering information section. No change in functional or electrical specification. Update the 8P3, 8X, 8MA2, and 8U3-1 package outline drawings and the disclaimer page.
8787D	04/2013	In the Page Write description, correct from eight to 16 data words. Update ordering code table, footers, and disclaimer page.
8787C	07/2012	Correct ordering codes: - AT24C04C-WWU11, Die Sale to AT24C04C-WWU11M, Wafer Sale. - AT24C08C-WWU11, Die Sale to AT24C08C-WWU11M, Wafer Sale. Remove WDT from ordering code detail. Update Atmel logos and disclaimer page.
8787B	05/2012	Remove preliminary status. Remove A <sub>0</sub> signal from the block diagram. I <sub>SB2</sub> parameter measured at 5.5V. In AC Characteristics table, changed 1.7V, 2.5V, 2.7V to 1.7 and 5.0V to 2.5V, 2.7V, 5.0V. Increase t <sub>i</sub> maximum value from 50ns to 100ns. Endurance parameter is studied at 3.3V, to +25°C, Page mode. Remove Serial Number Read from read operations. Update product markings. Update 8X and 8U3-1 package drawings. Update template.
8787A	10/2011	Initial document release.

